

Silicon Carbide (SiC) Sputtering Targets

Material Type	Silicon Carbide	Theoretical Density (g/cc)	3.22
Symbol	SiC	Z Ratio	**1.00
Melting Point (°C)	~2,700	Sputter	RF
Purity:	99.99%, 99.95%	Max Power Density	53
		(Watts/Square Inch)	
		Type of Bond	Indium